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50 V, 100 mA NPN/PNP Resistor-Equipped double Transistors (RET)

25 July 2017

Product data sheet

1. General description

NPN/PNP Resistor-Equipped double Transistors (RET) in an ultra small DFN1412-6 (SOT1268) leadless Surface-Mounted Device (SMD) plastic package.

NPN/NPN complement: PRMH13.

2. Features and benefits

- 100 mA output current capability
- Built-in bias resistors
- · Simplifies circuit design
- Reduces component count
- · Reduces pick and place costs
- · Low package height of 0.5 mm
- AEC-Q101 qualified

3. Applications

- Digital applications
- Cost-saving alternative to BC847/BC857 series in digital applications
- Control of IC inputs
- · Switching loads

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
Per transistor,	Per transistor, for the PNP transistor with negative polarity							
V _{CEO}	collector-emitter voltage	open base		-	-	50	V	
Io	output current			-	-	100	mA	
h _{FE}	DC current gain	V _{CE} = 5 V; I _C = 10 mA; T _{amb} = 25 °C		100	-	-		
R1	bias resistor 1	T _{amb} = 25 °C	[1]	3.3	4.7	6.1	kΩ	
R2/R1	bias resistor ratio		[1]	8	10	12		

^[1] See section "Test information" for resistor calculation and test conditions.



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	GND1	GND (emitter) TR1		O1 I2 GND2
2	I1	input (base) TR1	$\begin{bmatrix} 1 \\ 7 \end{bmatrix}$	
3	O2	output (collector) TR2	2 5	R1 R2
4	GND2	GND (emitter) TR2		TR1
5	12	input (base) TR2	3 0 4	R2 R1
6	01	output (collector) TR1	Transparent top view	
7	01	output (collector) TR1	DFN1412-6 (SOT1268)	GND1 I1 O2
8	O2	output (collector) TR2	,	aaa-007379

6. Ordering information

Table 3. Ordering information

Type number	Package	Package				
	Name	Description	Version			
PRMD13	DFN1412-6	plastic thermal enhanced ultra thin small outline package; no leads; 6 terminals; body: 1.4 mm x 1.2 mm x 0.47 mm	SOT1268			

7. Marking

Table 4. Marking codes

Type number	Marking code
PRMD13	B6

50 V, 100 mA NPN/PNP Resistor-Equipped double Transistors (RET)

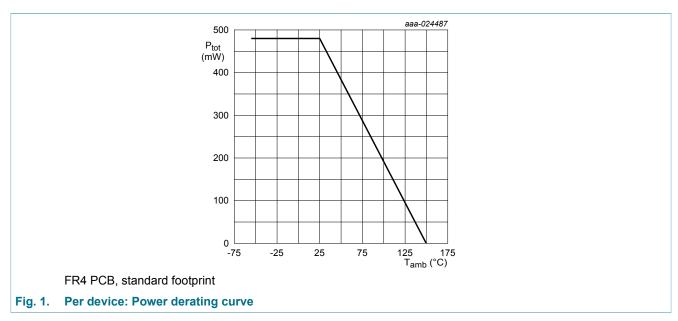
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transist	or, for the PNP transistor wit	h negative polarity				
V _{CBO}	collector-base voltage	open emitter		-	50	V
V_{CEO}	collector-emitter voltage	open base		-	50	V
V_{EBO}	emitter-base voltage	open collector		-	5	V
VI	input voltage	negative		-5	-	V
		positive		-	30	V
Io	output current			-	100	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	325	mW
Per device				'		'
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	480	mW
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.



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9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transis	tor					,	
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	385	K/W
Per device	,						
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	[1]	-	-	261	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

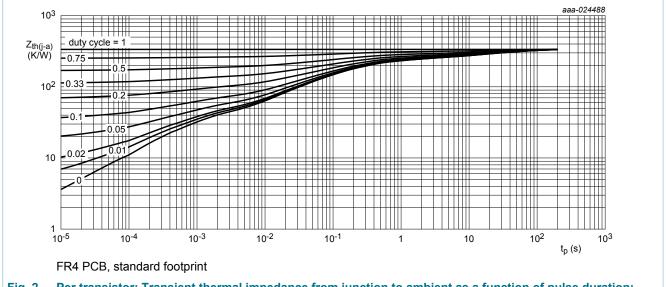


Fig. 2. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transist	or, for the PNP transistor v	vith negative polarity					
I _{CBO}	collector-base cut-off current (emitter open)	$V_{CB} = 50 \text{ V}; I_{E} = 0 \text{ A}; T_{amb} = 25 ^{\circ}\text{C}$		-	-	100	nA
I _{CEO}	collector-emitter cut-off	V_{CE} = 30 V; I_{B} = 0 A; T_{amb} = 25 °C		-	-	1	μΑ
	current (base open)	V_{CE} = 30 V; I_{B} = 0 A; T_{j} = 150 °C		-	-	5	μΑ
I _{EBO}	emitter-base cut-off current (collector open)	$V_{EB} = 5 \text{ V}; I_{C} = 0 \text{ A}; T_{amb} = 25 ^{\circ}\text{C}$		-	-	170	μA
h _{FE}	DC current gain	V_{CE} = 5 V; I_{C} = 10 mA; T_{amb} = 25 °C		100	-	-	
V _{CEsat}	collector-emitter saturation voltage	$I_C = 5 \text{ mA}; I_B = 0.25 \text{ mA}; T_{amb} = 25 ^{\circ}\text{C}$		-	-	100	mV
$V_{I(off)}$	off-state input voltage	V _{CE} = 5 V; I _C = 100 μA; T _{amb} = 25 °C		-	0.6	0.5	V
$V_{I(on)}$	on-state input voltage	V_{CE} = 0.3 V; I_{C} = 5 mA; T_{amb} = 25 °C		1.3	0.9	-	V
R1	bias resistor 1	T _{amb} = 25 °C	[1]	3.3	4.7	6.1	kΩ
R2/R1	bias resistor ratio		[1]	8	10	12	
C _C	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = 0 \text{ A}; i_e = 0 \text{ A};$ f = 1 MHz; $T_{amb} = 25 \text{ °C}$		-	-	2.5	pF
		V_{CB} = -10 V; I_{E} = 0 A; i_{e} = 0 A; f = 1 MHz; T_{amb} = 25 °C		-	-	3	pF
f _T	transition frequency	V_{CE} = 5 V; I_{C} = 10 mA; f = 100 MHz; T_{amb} = 25 °C	[2]	-	230	-	MHz
		V_{CE} = -5 V; I_{C} = -10 mA; f = 100 MHz; T_{amb} = 25 °C	[2]	-	180	-	MHz

^[1] See section "Test information" for resistor calculation and test conditions.

^[2] Characteristics of built-in transistor.

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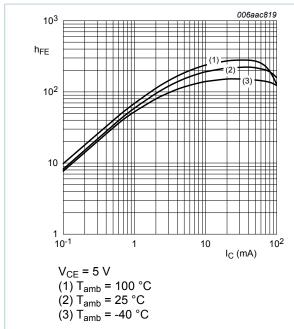
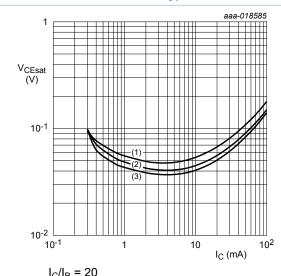


Fig. 3. NPN transistor: DC current gain as a function of collector current; typical values



 $I_C/I_B = 20$ (1) $T_{amb} = 100 \,^{\circ}C$ (2) $T_{amb} = 25 \,^{\circ}C$ (3) $T_{amb} = -40 \,^{\circ}C$

Fig. 5. NPN transistor: Collector-emitter saturation voltage as a function of collector current; typical values

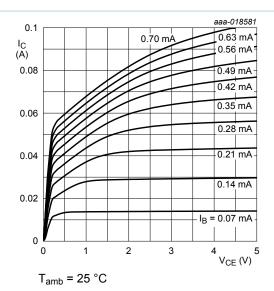
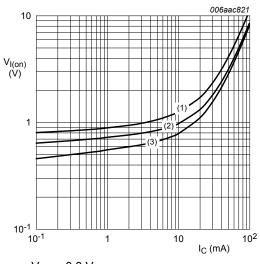


Fig. 4. NPN transistor: Collector current as a function of collector-emitter voltage; typical values

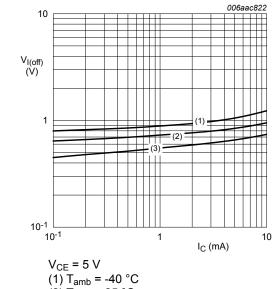


 $V_{CE} = 0.3 \text{ V}$ (1) $T_{amb} = -40 \,^{\circ}\text{C}$ (2) $T_{amb} = 25 \,^{\circ}\text{C}$ (3) $T_{amb} = 100 \,^{\circ}\text{C}$

Fig. 6. NPN transistor: On-state input voltage as a function of collector current; typical values

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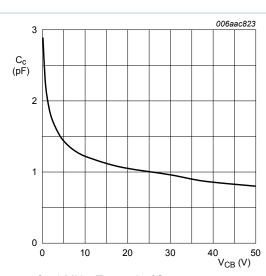
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(2) $T_{amb} = 25 \, ^{\circ}C$

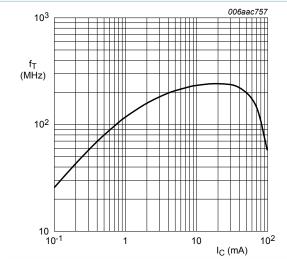
(3) $T_{amb} = 100 \, ^{\circ}C$

NPN transistor: Off-state input voltage as a Fig. 7. function of collector current; typical values



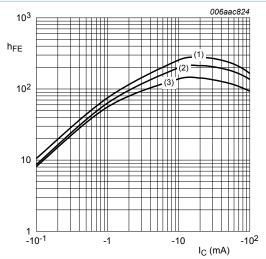
 $f = 1 MHz; T_{amb} = 25 °C$

Fig. 8. NPN transistor: Collector capacitance as a function of collector-base voltage; typical values



 V_{CE} = 5 V; T_{amb} = 25 °C

NPN transistor: Transition frequency as a Fig. 9. function of collector current; typical values of built-in transistor



V_{CE} = -5 V (1) T_{amb} = 100 °C (2) T_{amb} = 25 °C (3) T_{amb} = -40 °C

Fig. 10. PNP transistor: DC current gain as a function of collector current; typical values

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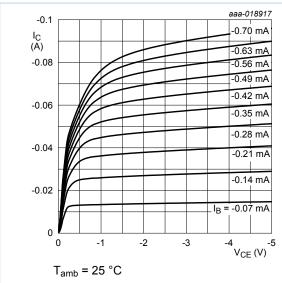
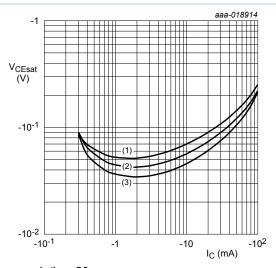
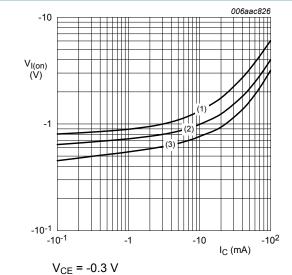


Fig. 11. PNP transistor: Collector current as a function of collector-emitter voltage; typical values



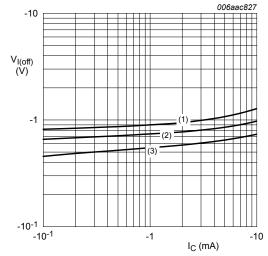
 $I_C/I_B = 20$ (1) $T_{amb} = 100 \,^{\circ}C$ (2) $T_{amb} = 25 \,^{\circ}C$ (3) $T_{amb} = -40 \,^{\circ}C$

Fig. 12. PNP transistor: Collector-emitter saturation voltage as a function of collector current; typical values



(1) T_{amb} = -40 °C (2) T_{amb} = 25 °C (3) T_{amb} = 100 °C

Fig. 13. PNP transistor: On-state input voltage as a function of collector current; typical values



 V_{CE} = -5 V (1) T_{amb} = -40 °C (2) T_{amb} = 25 °C (3) T_{amb} = 100 °C

Fig. 14. PNP transistor: Off-state input voltage as a function of collector current; typical values

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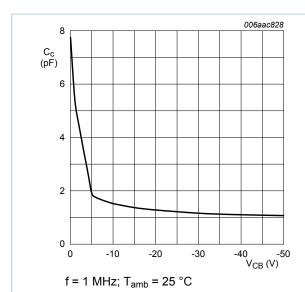


Fig. 15. PNP transistor: Collector capacitance as a function of collector-base voltage; typical values

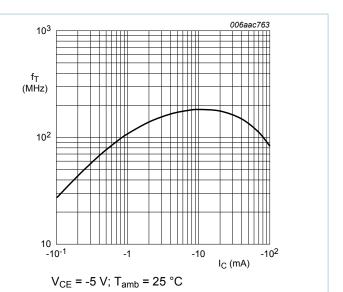


Fig. 16. PNP transistor: Transition frequency as a function of collector current; typical values of built-in transistor

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11. Test information

Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

Resistor calculation

· Calculation of bias resistor 1 (R1)

$$RI = \frac{V(I12) - V(I11)}{I12 - I11}$$

· Calculation of bias resistor ratio (R2/R1)

$$\frac{R2}{R1} = \frac{V(I14) - V(I13)}{R1 \cdot (I14 - I13)} - 1$$

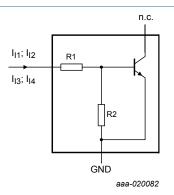


Fig. 17. NPN transistor: Resistor test circuit

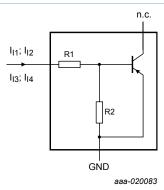


Fig. 18. PNP transistor: Resistor test circuit

Resistor test conditions

Table 8. Resistor test conditions

Per transistor; for the PNP transistor with negative polarity

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R1 (kΩ)	R2 (kΩ)	Test conditions			
		I _{I1}	I _{I2}	I ₁₃	I ₁₄
4.7	47	90 μΑ	140 μΑ	-55 μΑ	-105 μΑ

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12. Package outline

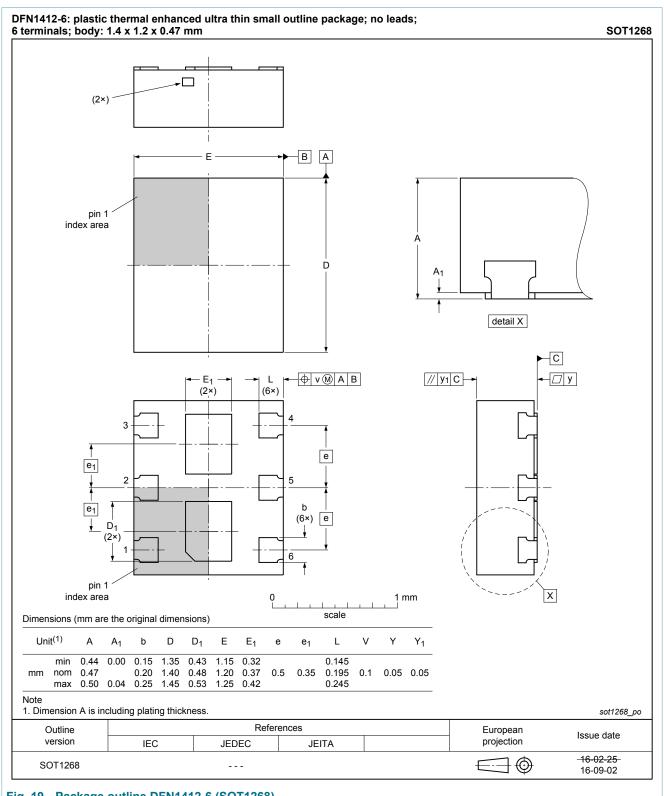
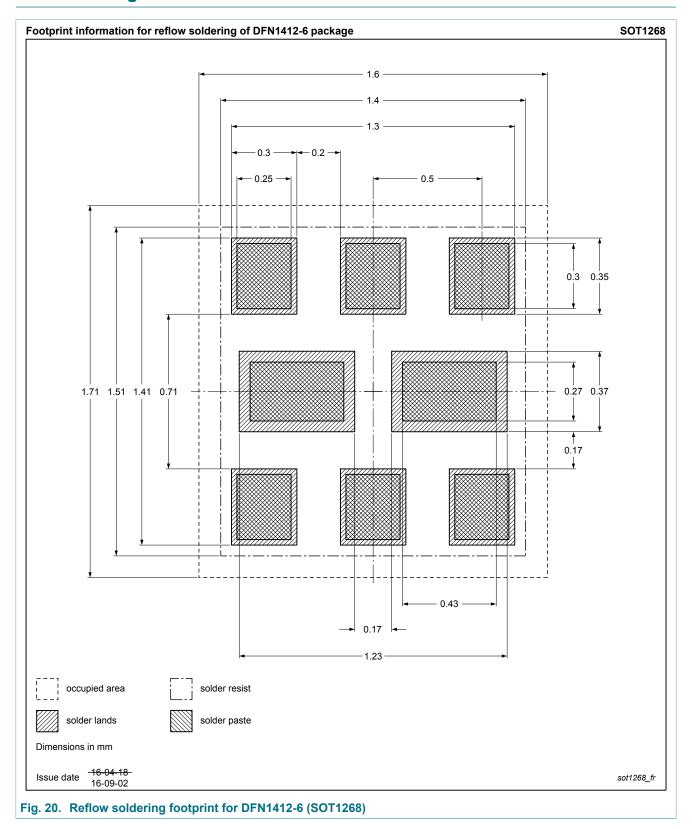


Fig. 19. Package outline DFN1412-6 (SOT1268)

50 V, 100 mA NPN/PNP Resistor-Equipped double Transistors (RET)

13. Soldering



50 V, 100 mA NPN/PNP Resistor-Equipped double Transistors (RET)

14. Revision history

Table 9. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PRMD13 v.1	20170725	Product data sheet	-	-

50 V, 100 mA NPN/PNP Resistor-Equipped double Transistors (RET)

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
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